74HC2G125; 74HCT2G125

Dual buffer/line driver; 3-state

Rev. 5 — 17 March 2014

Product data sheet

1. General description

The 74HC2G125; 74HC2G12 $\overline{5}$ are dual buffer/line drivers with 3-state outputs controlled by the output enable inputs (n \overline{OE}). Inputs include clamp diodes which enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - ◆ For 74HC2G125: CMOS level
 - ♦ For 74HCT2G125: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package					
	Temperature range	Name	Description	Version		
74HC2G125DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads;	SOT505-2		
74HCT2G125DP			body width 3 mm; lead length 0.5 mm			
74HC2G125DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads;	SOT765-1		
74HCT2G125DC			body width 2.3 mm			
74HC2G125GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads;	SOT996-2		
74HCT2G125GD			8 terminals; body 3 × 2 × 0.5 mm			



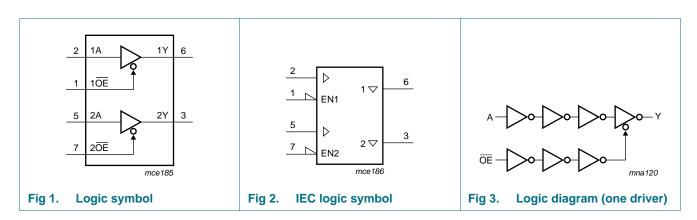
4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74HC2G125DP	H25
74HCT2G125DP	T25
74HC2G125DC	H25
74HCT2G125DC	T25
74HC2G125GD	H25
74HCT2G125GD	T25

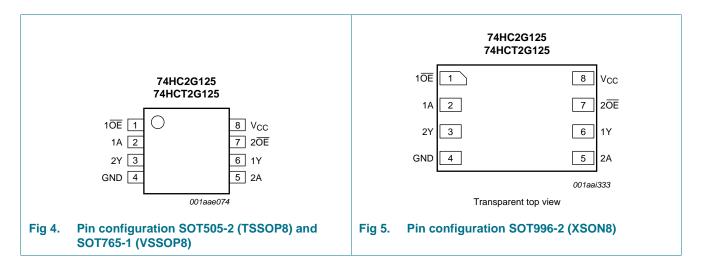
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



74HC_HCT2G125

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1 OE , 2 OE	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Control	Input	Output
nOE	nA	nY
L	L	L
L	Н	Н
Н	X	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	<u>[1]</u>	-	35	mA
I _{CC}	supply current			-	70	mA
I _{GND}	ground current			-70	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[2]</u>	-	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC	74HC2G125			74HCT2G125		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	T _{amb} =	–40 °C to	+85 °C	$T_{amb} = -40^{\circ}$	Unit	
			Min	Тур	Max	Min	Max	
74HC2G1	25							
V _{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}		V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
	voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}						
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.84	4.32	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.34	5.81	-	5.2	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A; V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
Iı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±1.0	-	±1.0	μΑ
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±5.0	-	±10	μΑ

 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	T _{amb} =	–40 °C to	+85 °C	$T_{amb} = -40^{\circ}$	Unit	
			Min	Тур	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μΑ
Cı	input capacitance		-	1.0	-	-	-	pF
Co	output capacitance		-	1.5	-	-	-	pF
74HCT2G	125							
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$						
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	V
		$I_{O} = -6.0 \text{ mA}$	3.84	4.32	-	3.7	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$						
	voltage	I _O = 20 μA	-	0	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}$	-	0.16	0.33	-	0.4	V
II	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	-	±1.0	μА
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	±5.0	-	±10	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ
Δl _{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A}$	-	-	375	-	410	μΑ
Cı	input capacitance		-	1.0	-	-	-	pF
Co	output capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions		-40 °C to	+85 °C	$T_{amb} = -40^{\circ}$	Unit	
			Min	Typ[1]	Max	Min	Max	
74HC2G	74HC2G125							
t _{pd}	propagation delay	nA to nY; see Figure 6						
		V _{CC} = 2.0 V	-	35	115	-	135	ns
		V _{CC} = 4.5 V	-	11	23	-	27	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	10	-	-	-	ns
		V _{CC} = 6.0 V	-	8	20	-	23	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \ pF$ unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions		T _{amb} =	–40 °C to	+85 °C	$T_{amb} = -40$	Unit	
				Min	Typ[1]	Max	Min	Max	
t _{en}	enable time	nOE to nY; see Figure 7	[2]						
		V _{CC} = 2.0 V		-	40	115	-	135	ns
		V _{CC} = 4.5 V		-	11	23	-	27	ns
		V _{CC} = 6.0 V		-	8	20	-	23	ns
t _{dis}	disable time	nOE to nY; see Figure 7	[2]						
		V _{CC} = 2.0 V		-	24	125	-	150	ns
		V _{CC} = 4.5 V		-	12	25	-	30	ns
		V _{CC} = 6.0 V		-	10	21	-	26	ns
t _t	transition	see Figure 6	[2]						
	time	V _{CC} = 2.0 V		-	18	75	-	90	ns
		V _{CC} = 4.5 V		-	6	15	-	18	ns
		V _{CC} = 6.0 V		-	5	13	-	15	ns
C _{PD}	power dissipation	per buffer; $V_I = GND$ to V_{CC}	[3]						
		output enabled		-	11	-	-	-	pF
	capacitance	output disabled		-	1	-	-	-	pF
74HCT20	G125								
t _{pd}	propagation	nA to nY; see Figure 6	[2]						
	delay	V _{CC} = 4.5 V		-	15	31	-	38	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	12	-	-	-	ns
t _{en}	enable time	nOE to nY; see Figure 7; V _{CC} = 4.5 V	[2]	-	15	35	-	42	ns
t _{dis}	disable time	nOE to nY; see Figure 7; V _{CC} = 4.5 V	[2]	-	15	31	-	38	ns
t _t	transition time	see <u>Figure 6</u> ; V _{CC} = 4.5 V	[2]	-	6	15	-	18	ns
C _{PD}	power dissipation	per buffer; $V_I = GND$ to $V_{CC} - 1.5$ V	[3]						
	capacitance	output enabled		-	11	-	-	-	pF
		output disabled		-	1	-	-	-	pF
		The state of the s					1	1	

- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .

 t_{en} is the same as t_{PZL} and t_{PZH} .

 t_{dis} is the same as t_{PLZ} and t_{PHZ} .

 t_{t} is the same as t_{THL} and $t_{TLH}. \label{eq:tt}$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

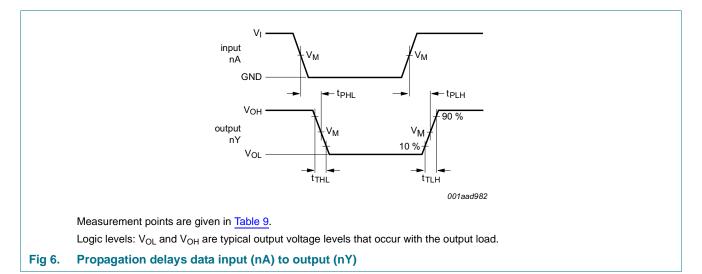
N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

74HC HCT2G125

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12. Waveforms and test circuit



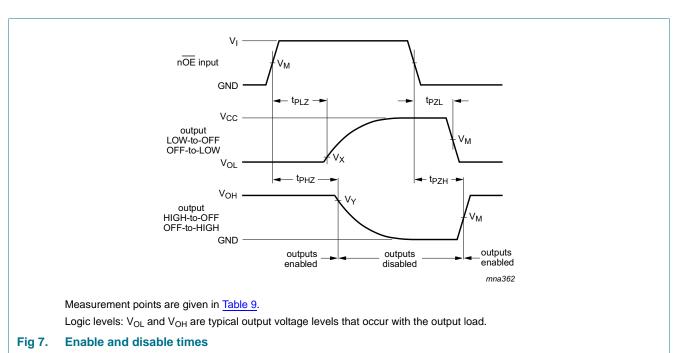
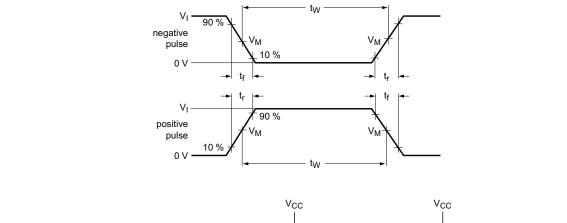
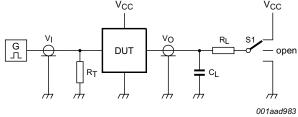


Table 9. Measurement points

Туре	Input	Output					
	V _M	V _M	V _X	V _Y			
74HC2G125	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V	V _{OH} – 0.3 V			
74HCT2G125	1.3 V	1.3 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V			





Test data is given in Table 10.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

Туре	Input		Load		S1 position		
	VI	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74HC2G125	V _{CC}	≤ 6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74HCT2G125	3 V	≤ 6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

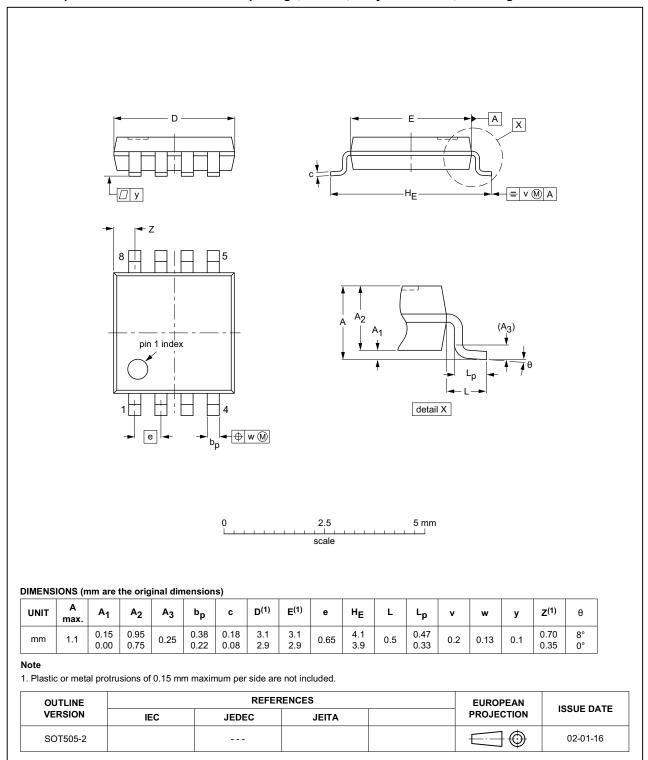


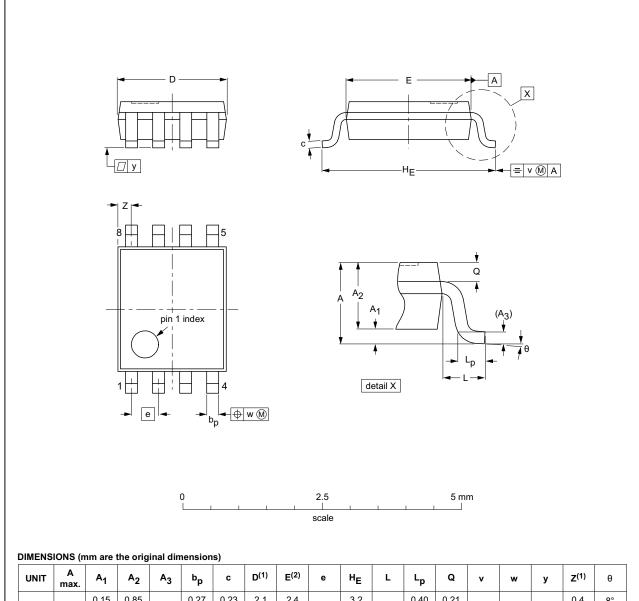
Fig 9. Package outline SOT505-2 (TSSOP8)

74HC_HCT2G125

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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT765-1		MO-187				02-06-07	

Fig 10. Package outline SOT765-1 (VSSOP8)

74HC_HCT2G125

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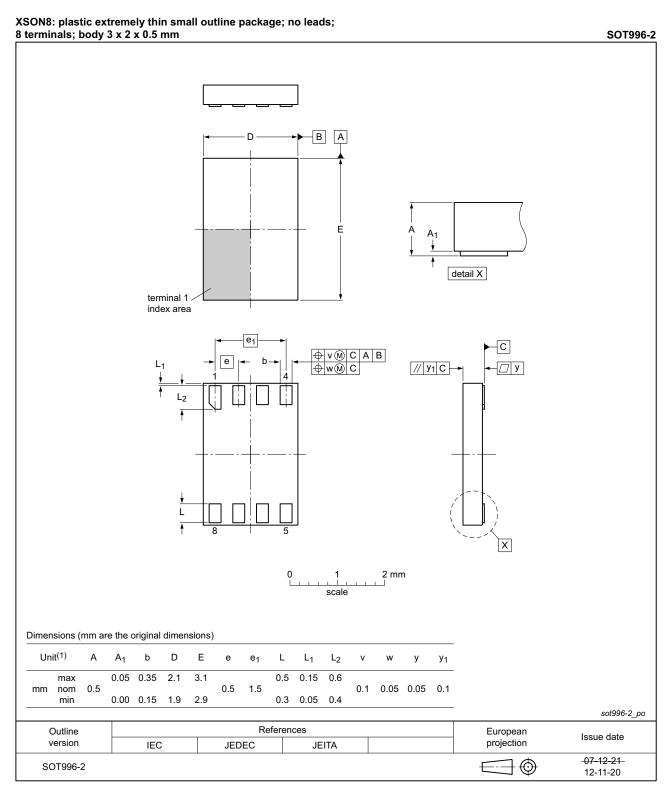


Fig 11. Package outline SOT996-2 (XSON8)

74HC_HCT2G125

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G125 v.5	20140317	Product data sheet	-	74HC_HCT2G125 v.4
Modifications:	For type numb	pers 74HC2G125GD and 74	HCT2G125GD XSON8L	I has changed to XSON8.
74HC_HCT2G125 v.4	20080704	Product data sheet	-	74HC_HCT2G125 v.3
74HC_HCT2G125 v.3	20060102	Product data sheet	-	74HC_HCT2G125 v.2
74HC_HCT2G125 v.2	20030303	Product specification	-	74HC_HCT2G125 v.1
74HC_HCT2G125 v.1	20030131	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition					
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.					
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.					
Product [short] data sheet	Production	This document contains the product specification.					

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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74HC_HCT2G125

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74HC2G125; 74HCT2G125

Dual buffer/line driver; 3-state

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18. Contents

1	General description
2	Features and benefits
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information
6.1	Pinning
6.2	Pin description
7	Functional description 3
8	Limiting values
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 5
12	Waveforms and test circuit
13	Package outline 9
14	Abbreviations
15	Revision history
16	Legal information
16.1	Data sheet status
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks14
17	Contact information 14
18	Contents

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